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Form PTO-1449 (MODIFIED) AUG 25 2003 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY. DOCKET NO. 039153-0472 (G1177)	SERIAL NO. 09/994,397
APPLICANT Besser et al.		
FILING DATE 11/26/2001		GROUP ART UNIT 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
MG	A1	6,534,865	03/18/2003	Lopatin et al.	257	751	
MG	A2	6,365,502	04/02/2002	Paranjpe et al.	438	622	
MG	A3	6,242,808	06/05/2001	Shimizu et al.	257	762	
MG	A4	6,225,221	05/01/2001	Ho et al.	438	678	
MG	A5	6,117,770	09/12/2000	Pramanick et al.	438	659	
MG	A6	6,090,710	07/18/2000	Andricacos et al.	438	687	
MG	A7	6,015,749	01/18/2000	Liu et al.	438	628	
MG	A8	2002/0109233	08/15/2002	Farrar	257	762	
MG	A9	2001/0035237	11/01/01	Nagano et al.	148	430	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
MG	A10	EP 1 094 515 A2	04/25/2001	EPO				
MG	A11	EP 1 039 531 A2	09/27/2000	EPO				
MG	A12	EP 1 039 531 A3	12/20/2000	EPO				
MG	A13	EP 0.567 867 A2	11/03/1993	EPO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

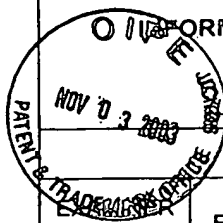
MG	A14	Dong Joon Kim et al, "New Method to Prepare W-B ⁺ -N Ternary Barrier to Cu diffusion by Implanting BF ₂ ⁺ Ions Into W-N Thin Film," J. Vac. Sci. Technol. B 17(4), July/Aug, 1999, pp. 1598-1601.
		W. F. McArthur et al., "Structural and Electrical Characterization of Si-Implanted Tin as a Diffusion Barrier for Cu Metallization," Mat. Res. Soc. Symp. Proc. Vol. 391, 1995, pp. 327-332.
MG	A16	PCT International Search Report, International Application No. PCT/US 02/32605, International Filing Date 11/10/2002 (7 pages).
		PCT International search Report, International Application No. PCT/US 02/32554, International Filing Date 11/10/2002 (5 pages).

EXAMINER

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U.S. PATENT DOCUMENTS

INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
MG	A1	6,521,532	02/18/2003	Cunningham			
MG	A2	6,500,749	12/31/2002	Liu et al.			
MG	A3	6,482,740	11/19/2002	Soininen et al.			
MG	A4	6,482,734	11/19/2002	Ha et al.			
MG	A5	6,465,867	10/15/2002	Bernard et al.			
MG	A6	6,461,675	10/08/2002	Paranjpe et al.			
MG	A7	6,423,633	07/23/2002	Tseng			

FOREIGN PATENT DOCUMENTS

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							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MG	A32	James A. Cunningham, "Improving Copper Interconnects: A Search for Useful Dopants," Semiconductor International, (April, 2000), pp. 1-8.

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3-1-04

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